

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	62	(US-20070030623-\$ or US-20060098362-\$ or US-20060286737-\$ or US-20030226996-\$ or US-20030178620-\$ or US-20040223288-\$ or US-20040184216-\$ or US-20030183866-\$).did. or (US-7064345-\$ or US-5705826-\$ or US-5892244-\$ or US-6087196-\$ or US-6992322-\$ or US-7193237-\$ or US-7198977-\$ or US-5500537-\$ or US-6586791-\$ or US-6331356-\$ or US-6890792-\$ or US-6219170-\$ or US-6555840-\$ or US-5206525-\$ or US-6950299-\$ or US-6999296-\$ or US-6865066-\$ or US-4449141-\$ or US-5038184-\$ or US-6703681-\$).did. or (US-3512052-\$ or US-3508123-\$).did. or (DE-10219905-\$).did. or (JP-2001085272-\$).did. or (JP-2004320022-\$ or DE-10219905-\$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 13:49
S2	5	(metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:00
S3	12170	(metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:01

S4	7427	(metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:01
S5	2171	(metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor).ab,ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:01
S6	2170	(metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:02
S7	116	(metal or conductive or electrode) and semiconductor near3 layer and voltage with (varied or varing or variable or vary) capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:02
S8	2043	(metal or conductive or electrode) and semiconductor near3 layer and voltage with capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:12
S9	94	(metal or conductive or electrode) and semiconductor near3 layer and voltage with (variable or tunable or controlable or trimmable) capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:20

S10	192	(metal or conductive or electrode) and semiconductor near3 layer and voltage with (variable or tunable or controlable or trimmable) with capacitance and (varactor or capacitor or condensor).ab,ti. not electrolytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:21
S11	380	(metal or conductive or electrode) and semiconductor near3 layer and voltage with (varied or varing or variable or vary) with capacitance and (varactor or capacitor or condensor).ab,ti. not eletrolytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:21
S12	6408	metal semiconductor metal or MSM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:42
S13	1410	metal semiconductor metal or MSM and (varactor or capcitor or condensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:42
S14	1696	metal semiconductor metal or MSM and (varactor or capacitor or condensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:42
S15	566	(metal semiconductor metal or MSM) and (varactor or capacitor or condensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 14:44
S16	1	("6414369").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/02/12 14:46
S18	2	("5614727" "5719647").PN. OR ("6414369").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/02/12 15:00
S19	9419	pn junction and (varactor or capacitor or condensor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 15:03
S20	2047	pn junction and (varactor or capacitor or condensor).ab,ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 15:03

S21	91	pn junction and (varactor or capacitor or condensor).ab,ti. and "361". clas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 15:04
S22	50	(metal semiconductor metal or MSM) and (varactor or capacitor or condensor).ab,ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 15:07
S23	145	pn and (varactor or capacitor or condensor).ab,ti. and "361". clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 15:11
S24	48	pn same semiconductor and (varactor or capacitor or condensor).ab,ti. and "361". clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/12 15:11
S25	1	("20040184216"). PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/02/17 08:12
S26	4795	semiconduct\$4 with (insulat\$4 or dielectric) with frequency	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 08:28
S27	1588	semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (capacitor or condensor or varactor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 08:28
S28	1148	semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (capacitor or condensor or varactor) and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 08:28
S29	728	semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (capacitor or condensor or varactor).ab,ti,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 08:29
S30	67	semiconduct\$4 with (insulat\$4 or dielectric) with frequency and (varactor).ab,ti,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 08:31
S31	8	semiconduct\$4 with (insulat\$4 or dielectric) with frequency with act and (varactor or capacitor or condensor).ab,ti,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 09:04
S32	46	semiconduct\$4 with (insulat\$4 or dielectric) with frequency with act	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	ADJ	ON	2009/02/17 09:07

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